	т			
L Number	Hits	Search Text	DB	Time stamp
-	207	(mfs MFMIS) with (ferroelectric ferro-electric)	USPAT;	2002/06/05
		lello electico	US-PGPUB; EPO; JPO;	12:44
			DERWENT;	
_	109	//mf= MEMTG) with /5	IBM_TDB	
_	109	((mfs MFMIS) with (ferroelectric ferro-electric)) and (writ\$3 program\$4)	USPAT; US-PGPUB;	2002/06/06
		and (read\$3)	EPO; JPO;	10:59
			DERWENT;	
_	12	(((mfs MFMIS) with (ferroelectric	IBM_TDB USPAT;	2002/06/05
	1	ferro-electric)) and (writ\$3 program\$4)	US-PGPUB;	2002/06/05
		and (read\$3)) and ((current adj3 chang\$3)	EPO; JPO;	13.00
		same (Vds voltage))	DERWENT;	
_	14498	(mfs MFMIS) (metal adj4 (ferroelectric	IBM_TDB USPAT;	2002/06/05
		ferro-electric) adj4 insulator)	US-PGPUB;	13:06
			EPO; JPO;	
			DERWENT; IBM TDB	
-	3093	((mfs MFMIS) (metal adj4 (ferroelectric	USPAT;	2002/06/05
		ferro-electric) adj4 insulator)) and	US-PGPUB;	13:08
		(writ\$3 program\$4) and (read\$3)	EPO; JPO;	
			DERWENT; IBM TDB	
-	29		USPAT;	2002/06/05
		ferro-electric) adj4 insulator)) and	US-PGPUB;	12:55
		(writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3) same (Vds	EPO; JPO; DERWENT;	
		voltage))	IBM TDB	
_	18496	(mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/05
		(ferroelectric ferro-electric) adj3 insulator)	US-PGPUB;	13:07
		Insulatory	EPO; JPO; DERWENT;	
			IBM TDB	
-	3302	((mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/05
		(ferroelectric ferro-electric) adj3 insulator)) and (writ\$3 program\$4) and	US-PGPUB; EPO; JPO;	13:09
		(read\$3)	DERWENT;	
	20	III S ADTO ACTION IN A STATE OF THE STATE OF	IBM_TDB	
_	29	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3	USPAT; US-PGPUB;	2002/06/06 16:58
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	16:56
		<pre>(read\$3)) and ((current adj3 chang\$3)</pre>	DERWENT;	
_	10	same (Vds voltage)) (((mfs MFIS MFMIS) (metal adj3	IBM_TDB	0000/05/05
İ	10	(ferroelectric ferro-electric) adj3	USPAT; US-PGPUB;	2002/06/06 16:55
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	10.00
		(read\$3)) and ((current adj3 chang\$3)	DERWENT;	
		<pre>same (Vds voltage)) and (ferroelectric adj3 capacitor)</pre>	IBM_TDB	
-	10	((((mfs MFIS MFMIS) (metal adj3	USPAT;	2002/06/06
		(ferroelectric ferro-electric) adj3	US-PGPUB;	16:55
		<pre>insulator)) and (writ\$3 program\$4) and (read\$3)) and ((current adj3 chang\$3)</pre>	EPO; JPO;	
		same (Vds voltage)) and (ferroelectric	DERWENT; IBM TDB	
		adj3 capacitor)) and (gate adj3		
_	4	electrode)		0000/05/55
	4	(((mfs MFIS MFMIS) (metal adj3 (ferroelectric ferro-electric) adj3	USPAT; US-PGPUB;	2002/06/06
		insulator)) and (writ\$3 program\$4) and	EPO; JPO;	17.00
		(read\$3)) and ((current adj3 chang\$3)	DERWENT;	
		same (Vds voltage)) and ((ferroelectric adj3 capacitor) with (gate adj3	IBM_TDB	
		electrode))		
			L	L.,,

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	7 205	1/5		
-	205	((ferroelectric adj3 capacitor) with	USPAT;	2002/06/06
		(gate adj3 electrode))	US-PGPUB;	16:58
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	40		USPAT;	2002/06/06
		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	16:58
		MFMIS)	EPO; JPO;	10.30
			DERWENT;	
	1			
_	32	///formoologtmin add a new with	IBM_TDB	
_	32		USPAT;	2002/06/06
		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	17:00
		MFMIS)) and (writ\$3 program\$4) and	EPO; JPO;	1
		(read\$3)	DERWENT;	
			IBM TDB	
-	16	(((((ferroelectric adj3 capacitor) with	USPAT;	2002/06/06
1		(gate adj3 electrode))) and (mfs MFIS	US-PGPUB;	17:00
	-	MFMIS)) and (writ\$3 program\$4) and		17:00
i		(read(2)) and ((farmall state)	EPO; JPO;	
		(read\$3)) and ((ferroelectric	DERWENT;	
ł		ferro-electric) adj3 insulator)	IBM_TDB	
_	5690	read\$3 same ((voltage potential bias)	USPAT;	2003/03/20
1		with drain with source)	US-PGPUB;	11:17
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	574	((unsaturat\$3 non-saturat\$3) near3	· —	3003/03/30
	3,4	region) and (gaturates mans mades	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)	US-PGPUB;	12:17
			EPO; JPO;	
	İ		DERWENT;	
			IBM TDB	
-	22		USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:19
	i	(nonvolatile non-volatile)	EPO; JPO;	11.19
		(voice of the control of the contro		
	<u> </u>		DERWENT;	1
_	2835	(IBM_TDB	
_	2835	(read\$3 same ((voltage potential bias)	USPAT;	2003/03/20
		with drain with source)) and (nonvolatile	US-PGPUB;	11:20
		non-volatile)	EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	5	((((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and		
		(nonvolatile non-volatile)) and ((read\$3	US-PGPUB;	11:23
		same (/voltage notontial bird) with	EPO; JPO;	
1	1	same ((voltage potential bias) with drain	DERWENT;	
		with source)) and (nonvolatile	IBM_TDB	
		non-volatile))		
-	124614	((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	11:25
		nonvolatile	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	22	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and		1 ' ' 1
		///MEG MEMIC formal studies region)) and	US-PGPUB;	11:25
	[(((MFS MFMIS ferroelectric) near3	EPO; JPO;	
		transistor) FeRAM non-volatile	DERWENT;	
		nonvolatile)	IBM_TDB	
-	1	, ((((acaracys) iicars	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
		(((MFS MFMIS ferroelectric) near3	EPO; JPO;	
		transistor) FeRAM non-volatile	DERWENT;	
		nonvolatile)) and ((read\$3 with data with		
		(apples norms (residence to a control data with	IBM_TDB	
		(appl\$3 near3 (voltage bias potential))		
		with source with drain))		
-	1	(((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:27
		((read\$3 with data with (appl\$3 near3	EPO; JPO;	
		(voltage bias potential)) with source	DERWENT;	
		with drain))	· ·	
L	·		IBM_TDB	

	224	(reads) with data with (area)	Tions	
-	224	(read\$3 with data with (appl\$3 near3 (voltage bias potential)) with source	USPAT;	2003/03/20
		(voltage bias potential)) with source with drain)	US-PGPUB; EPO; JPO;	11:30
		with diality	DERWENT;	
			IBM TDB	
-	181	(((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
		transistor) FeRAM non-volatile	US-PGPUB;	12:16
		nonvolatile) and ((read\$3 with data with	EPO; JPO;	
	İ	<pre>(appl\$3 near3 (voltage bias potential))</pre>	DERWENT;	
		with source with drain))	IBM_TDB	
_	1		USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and	US-PGPUB;	11:29
		((((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile	EPO; JPO;	
		nonvolatile) and ((read\$3 with data with	DERWENT; IBM TDB	
		(appl\$3 near3 (voltage bias potential))	1511_105	
		with source with drain)))		
-	1669	read\$3 same ((appl\$3 near3 (voltage bias	USPAT;	2003/03/20
		potential)) with source with drain)	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
	_	///	IBM_TDB	
-	3	(((==================================	USPAT;	2003/03/20
		region) and (saturat\$3 near3 region)) and (read\$3 same ((appl\$3 near3 (voltage bias	US-PGPUB;	11:45
		potential)) with source with drain))	EPO; JPO;	[
			DERWENT; IBM TDB	
-	11	((unsaturat\$3 non-saturat\$3) near3	USPAT;	2003/03/20
1		region) with read\$3	US-PGPUB;	11:53
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
_	1	((() Included the state of the state	USPAT;	2003/03/20
		region) with read\$3) and (non-volatile nonvolatile)	US-PGPUB;	11:52
		Honvoiacije	EPO; JPO; DERWENT;	
	:		IBM TDB	
_	3769	(unsaturat\$3 non-saturat\$3) with read\$3	USPAT;	2003/03/20
			US-PGPUB;	11:53
			EPO; JPO;	
i			DERWENT;	
	3770	(IBM_TDB	
_	3779	<pre>(unsaturat\$3 non-saturat\$3) with read\$3</pre>	USPAT;	2003/03/20
		MICH TEGUĆA	US-PGPUB;	11:53
			EPO; JPO; DERWENT;	
			IBM TDB	
- '	200	((unsaturat\$3 non-saturat\$3 nonsaturat\$3)	USPAT;	2003/03/20
		with read\$3) and (non-volatile	US-PGPUB;	11:54
	j	nonvolatile)	EPO; JPO;	
			DERWENT;	
_	200	///MES MEMIS Formanis attains and an	IBM_TDB	
_	200	(((MFS MFMIS ferroelectric) near3 transistor) FeRAM non-volatile	USPAT;	2003/03/20
		nonvolatile) and (((unsaturat\$3	US-PGPUB; EPO; JPO;	12:04
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))	IBM TDB	
-	28	((((MFS MFMIS ferroelectric) near3	USPAT;	2003/03/20
]		transistor) FeRAM non-volatile	US-PGPUB;	12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
1		<pre>and (non-volatile nonvolatile))) and (read reading)</pre>	IBM_TDB	
_	8	(((((MFS MFMIS ferroelectric) near3	יייעם אווי.	2002/02/20
	9	transistor) FeRAM non-volatile	USPAT; US-PGPUB;	2003/03/20 12:09
		nonvolatile) and (((unsaturat\$3	EPO; JPO;	12.03
		non-saturat\$3 nonsaturat\$3) with read\$3)	DERWENT;	
		and (non-volatile nonvolatile))) and	IBM TDB	
[l		(read reading)) and memory		

-	1	((read\$3 with data with (appl\$3 near3	USPAT;	2003/03/20
		(voltage bias potential)) with source	US-PGPUB;	12:19
		with drain)) and ((unsaturat\$3	EPO; JPO;	
	İ	non-saturat\$3 nonsaturat\$3) near3 region)	DERWENT;	į l
			IBM TDB	
-	1	read\$3 with (unsaturat\$3 non-saturat\$3	USPAT;	2003/03/20
		nonsaturat\$3) with (current near3	US-PGPUB;	12:20
	1	detect\$3)	EPO; JPO;	
			DERWENT;	
			IBM TDB	